

# Johann P Reithmaier

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

402  
papers

9,713  
citations

40  
h-index

85  
g-index

478  
ext. papers

10,918  
ext. citations

3  
avg, IF

5.76  
L-index

#	Paper	IF	Citations
402	High optical gain in InP-based quantum-dot material monolithically grown on silicon emitting at telecom wavelengths. <i>Semiconductor Science and Technology</i> , <b>2022</b> , 37, 055005	1.8	0
401	Optical Quality of InAs/InP Quantum Dots on Distributed Bragg Reflector Emitting at 3rd Telecom Window Grown by Molecular Beam Epitaxy. <i>Materials</i> , <b>2021</b> , 14,	3.5	1
400	Spin memory effect in charged single telecom quantum dots: erratum. <i>Optics Express</i> , <b>2021</b> , 29, 36460	3.3	
399	Azido-Functionalized Aromatic Phosphonate Esters in POSS-Cage-Supported Lanthanide Ion (Ln = La, Nd, Dy, Er) Coordination. <i>Inorganic Chemistry</i> , <b>2021</b> , 60, 5297-5309	5.1	3
398	1.5- $\mu\text{m}$ Indium Phosphide-Based Quantum Dot Lasers and Optical Amplifiers: The Impact of Atom-Like Optical Gain Material for Optoelectronics Devices. <i>IEEE Nanotechnology Magazine</i> , <b>2021</b> , 15, 23-36	1.7	2
397	InP-based single-photon sources operating at telecom C-band with increased extraction efficiency. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 221101	3.4	5
396	Magneto-Optical Characterization of Trions in Symmetric InP-Based Quantum Dots for Quantum Communication Applications. <i>Materials</i> , <b>2021</b> , 14,	3.5	5
395	Quantum-Dot Based Vertical External-Cavity Surface-Emitting Lasers With High Efficiency. <i>IEEE Photonics Technology Letters</i> , <b>2021</b> , 33, 719-722	2.2	
394	On the principle operation of tunneling injection quantum dot lasers. <i>Progress in Quantum Electronics</i> , <b>2021</b> , 100362	9.1	3
393	Spin memory effect in charged single telecom quantum dots. <i>Optics Express</i> , <b>2021</b> , 29, 34024-34034	3.3	2
392	Influence of surface termination of ultrananocrystalline diamond films coated on titanium on response of human osteoblast cells: A proteome study. <i>Materials Science and Engineering C</i> , <b>2021</b> , 128, 112289	8.3	1
391	Optical and Electronic Properties of Symmetric InAs/(In,Al,Ga)As/InP Quantum Dots Formed by Ripening in Molecular Beam Epitaxy: A Potential System for Broad-Range Single-Photon Telecom Emitters. <i>Physical Review Applied</i> , <b>2020</b> , 14,	4.3	4
390	Mode properties of telecom wavelength InP-based high-(Q/V) L4/3 photonic crystal cavities. <i>Nanotechnology</i> , <b>2020</b> , 31, 315703	3.4	4
389	Resonant and Nonresonant Tunneling Injection Processes in Quantum Dot Optical Gain Media. <i>ACS Photonics</i> , <b>2020</b> , 7, 602-606	6.3	2
388	Novel Ultra Localized and Dense Nitrogen Delta-Doping in Diamond for Advanced Quantum Sensing. <i>Nano Letters</i> , <b>2020</b> , 20, 3192-3198	11.5	12
387	Temperature resistant fast InGaAs / GaAs quantum dot saturable absorber for the epitaxial integration into semiconductor surface emitting lasers. <i>Optics Express</i> , <b>2020</b> , 28, 20954-20966	3.3	2
386	Fabrication of Diamond AFM Tips for Quantum Sensing. <i>NATO Science for Peace and Security Series B: Physics and Biophysics</i> , <b>2020</b> , 171-185	0.2	0

385	High-Purity Triggered Single-Photon Emission from Symmetric Single InAs/InP Quantum Dots around the Telecom C-Band Window. <i>Advanced Quantum Technologies</i> , <b>2020</b> , 3, 1900082	4.3	16
384	Functionalised phosphonate ester supported lanthanide (Ln = La, Nd, Dy, Er) complexes. <i>Dalton Transactions</i> , <b>2020</b> , 49, 16683-16692	4.3	2
383	Fabrication and Characterization of Single-Crystal Diamond Membranes for Quantum Photonics with Tunable Microcavities. <i>Micromachines</i> , <b>2020</b> , 11,	3.3	3
382	Development of a Planarization Process for the Fabrication of Nanocrystalline Diamond Based Photonic Structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2019</b> , 216, 1900314	1.6	3
381	Fabrication of Nanopillars on Nanocrystalline Diamond Membranes for the Incorporation of Color Centers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2019</b> , 216, 1900233	1.6	2
380	Comparison between InP-based quantum dot lasers with and without tunnel injection quantum well and the impact of rapid thermal annealing. <i>Journal of Crystal Growth</i> , <b>2019</b> , 516, 34-39	1.6	2
379	Optimization of size uniformity and dot density of In <sub>x</sub> Ga <sub>1-x</sub> As/GaAs quantum dots for laser applications in 1 μm wavelength range. <i>Journal of Crystal Growth</i> , <b>2019</b> , 517, 1-6	1.6	3
378	Antimicrobial propensity of ultrananocrystalline diamond films with embedded silver nanodroplets. <i>Diamond and Related Materials</i> , <b>2019</b> , 93, 168-178	3.5	6
377	Comparison of quantum dot lasers with and without tunnel-injection quantum well <b>2019</b> ,		2
376	Narrow Linewidth InAs/InP Quantum Dot DFB Laser <b>2019</b> ,		2
375	Fabrication of highly dense arrays of nanocrystalline diamond nanopillars with integrated silicon-vacancy color centers during the growth. <i>Optical Materials Express</i> , <b>2019</b> , 9, 4545	2.6	4
374	Large linewidth reduction in semiconductor lasers based on atom-like gain material. <i>Optica</i> , <b>2019</b> , 6, 1071	8.6	25
373	MOICANA: monolithic cointegration of QD-based InP on SiN as a versatile platform for the demonstration of high-performance and low-cost PIC transmitters <b>2019</b> ,		1
372	Excited states of neutral and charged excitons in single strongly asymmetric InP-based nanostructures emitting in the telecom C band. <i>Physical Review B</i> , <b>2019</b> , 100,	3.3	6
371	Coherent light matter interactions in nanostructure based active semiconductor waveguides operating at room temperature. <i>Applied Physics Reviews</i> , <b>2019</b> , 6, 041317	17.3	1
370	Deterministic Arrays of Epitaxially Grown Diamond Nanopyramids with Embedded Silicon-Vacancy Centers. <i>Advanced Optical Materials</i> , <b>2019</b> , 7, 1800715	8.1	11
369	Photonic engineering of highly linearly polarized quantum dot emission at telecommunication wavelengths. <i>Physical Review B</i> , <b>2018</b> , 97,	3.3	9
368	Telecom wavelength single quantum dots with very small excitonic fine-structure splitting. <i>Applied Physics Letters</i> , <b>2018</b> , 112, 172102	3.4	25

367	Growth and optical characteristics of InAs quantum dot structures with tunnel injection quantum wells for 1.55 $\mu\text{m}$ high-speed lasers. <i>Journal of Crystal Growth</i> , <b>2018</b> , 491, 20-25	1.6	8
366	Temperature stability of static and dynamic properties of 1.55 $\mu\text{m}$ quantum dot lasers. <i>Optics Express</i> , <b>2018</b> , 26, 6056-6066	3.3	33
365	Strongly temperature-dependent recombination kinetics of a negatively charged exciton in asymmetric quantum dots at 1.55 $\mu\text{m}$ . <i>Applied Physics Letters</i> , <b>2018</b> , 113, 043103	3.4	4
364	Carrier transfer efficiency and its influence on emission properties of telecom wavelength InP-based quantum dot - quantum well structures. <i>Scientific Reports</i> , <b>2018</b> , 8, 12317	4.9	5
363	Homoepitaxial Diamond Structures with Incorporated SiV Centers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2018</b> , 215, 1800371	1.6	6
362	On the relationship between electrical and electro-optical characteristics of InAs/InP quantum dot lasers. <i>Journal of Applied Physics</i> , <b>2018</b> , 124, 054501	2.5	4
361	High Performance 1550 nm Quantum Dot Semiconductor Optical Amplifiers Operating at 25-100 $^{\circ}\text{C}$ <b>2018</b> ,		2
360	Control of Dynamic Properties of InAs/InAlGaAs/InP Hybrid Quantum Well-Quantum Dot Structures Designed as Active Parts of 1.55 $\mu\text{m}$ Emitting Lasers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2018</b> , 215, 1700455	1.6	7
359	Spectral Characteristics of Narrow Linewidth InAs/InP Quantum Dot Distributed Feedback Lasers <b>2018</b> ,		1
358	III $\text{V}$ on Silicon Nanocomposites. <i>Semiconductors and Semimetals</i> , <b>2018</b> , 27-42	0.6	2
357	Electron and hole spin relaxation in InP-based self-assembled quantum dots emitting at telecom wavelengths. <i>Physical Review B</i> , <b>2018</b> , 98,	3.3	2
356	Nanostructured modified ultrananocrystalline diamond surfaces as immobilization support for lipases. <i>Diamond and Related Materials</i> , <b>2018</b> , 90, 32-39	3.5	2
355	Carrier dynamics in a tunneling injection quantum dot semiconductor optical amplifier. <i>Physical Review B</i> , <b>2018</b> , 98,	3.3	11
354	Quantum Information Technology and Sensing Based on Color Centers in Diamond. <i>NATO Science for Peace and Security Series B: Physics and Biophysics</i> , <b>2018</b> , 193-214	0.2	
353	Carrier relaxation bottleneck in type-II InAs/InGaAlAs/InP(001) coupled quantum dots-quantum well structure emitting at 1.55 $\mu\text{m}$ . <i>Applied Physics Letters</i> , <b>2018</b> , 112, 221901	3.4	6
352	Ramsey fringes in a room-temperature quantum-dot semiconductor optical amplifier. <i>Physical Review B</i> , <b>2018</b> , 97,	3.3	5
351	Telecom wavelength emitting single quantum dots coupled to InP-based photonic crystal microcavities. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 031101	3.4	19
350	High-bandwidth temperature-stable 1.55- $\mu\text{m}$ quantum dot lasers <b>2017</b> ,		4

349	Carrier delocalization in InAs/InGaAlAs/InP quantum-dash-based tunnel injection system for 1.55 $\mu\text{m}$ emission. <i>AIP Advances</i> , <b>2017</b> , 7, 015117	1.5	10
348	Ultra-fast charge carrier dynamics across the spectrum of an optical gain media based on InAs/AlGaInAs/InP quantum dots. <i>AIP Advances</i> , <b>2017</b> , 7, 035122	1.5	8
347	Widely tunable narrow-linewidth 1.5 $\mu\text{m}$ light source based on a monolithically integrated quantum dot laser array. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 181103	3.4	18
346	Patterning of the surface termination of ultrananocrystalline diamond films for guided cell attachment and growth. <i>Surface and Coatings Technology</i> , <b>2017</b> , 321, 229-235	4.4	18
345	Lateral carrier diffusion in InGaAs/GaAs coupled quantum dot-quantum well system. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 221104	3.4	6
344	The issue of 0D-like ground state isolation in GaAs- and InP-based coupled quantum dots-quantum well systems. <i>Journal of Physics: Conference Series</i> , <b>2017</b> , 906, 012019	0.3	1
343	Exciton lifetime and emission polarization dispersion in strongly in-plane asymmetric nanostructures. <i>Physical Review B</i> , <b>2017</b> , 96,	3.3	18
342	Interplay of morphology, composition, and optical properties of InP-based quantum dots emitting at the 1.55 $\mu\text{m}$ telecom wavelength. <i>Physical Review B</i> , <b>2017</b> , 96,	3.3	8
341	Confinement regime in self-assembled InAs/InAlGaAs/InP quantum dashes determined from exciton and biexciton recombination kinetics. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 253106	3.4	8
340	. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2017</b> , 23, 1-3	3.8	44.2
339	Static and dynamic characteristics of an InAs/InP quantum-dot optical amplifier operating at high temperatures. <i>Optics Express</i> , <b>2017</b> , 25, 27262-27269	3.3	7
338	Acceleration of the nonlinear dynamics in p-doped indium phosphide nanoscale resonators. <i>Optics Letters</i> , <b>2017</b> , 42, 795-798	3	4
337	InAs on InP Quantum Dashes as Single Photon Emitters at the Second Telecommunication Window: Optical, Kinetic, and Excitonic Properties. <i>Acta Physica Polonica A</i> , <b>2017</b> , 132, 382-386	0.6	2
336	1.5 $\mu\text{m}$ quantum dot lasers for data and telecom applications <b>2016</b> ,		2
335	Large anisotropy of electron and hole g factors in infrared-emitting InAs/InAlGaAs self-assembled quantum dots. <i>Physical Review B</i> , <b>2016</b> , 93,	3.3	17
334	Temperature-Insensitive High-Speed Directly Modulated 1.55- $\mu\text{m}$ Quantum Dot Lasers. <i>IEEE Photonics Technology Letters</i> , <b>2016</b> , 28, 2451-2454	2.2	20
333	Excitonic fine structure and binding energies of excitonic complexes in single InAs quantum dashes. <i>Physical Review B</i> , <b>2016</b> , 94,	3.3	16
332	(Invited) III-V / Si Integration for Photonics. <i>ECS Transactions</i> , <b>2016</b> , 72, 171-179	1	5

331	Coherent photocurrent spectroscopy of single InP-based quantum dots in the telecom band at 1.5 $\mu\text{m}$ . <i>Applied Physics B: Lasers and Optics</i> , <b>2016</b> , 122, 1	1.9	3
330	Incorporation and study of SiV centers in diamond nanopillars. <i>Diamond and Related Materials</i> , <b>2016</b> , 64, 64-69	3.5	21
329	Probing the carrier transfer processes in a self-assembled system with In <sub>0.3</sub> Ga <sub>0.7</sub> As/GaAs quantum dots by photoluminescence excitation spectroscopy. <i>Superlattices and Microstructures</i> , <b>2016</b> , 93, 214-220 <sup>2.8</sup>		
328	Narrow-linewidth 1.5 $\mu\text{m}$ quantum dot distributed feedback lasers <b>2016</b> ,		3
327	High-speed directly modulated 1.5 $\mu\text{m}$ quantum dot lasers <b>2016</b> ,		4
326	Effect of Dielectric Medium Anisotropy on the Polarization Degree of Emission from a Single Quantum Dash. <i>Acta Physica Polonica A</i> , <b>2016</b> , 129, A-48-A-52	0.6	2
325	1.5 $\mu\text{m}$ quantum dot laser material with high temperature stability of threshold current density and external differential efficiency <b>2016</b> ,		6
324	Coherent control in room-temperature quantum dot semiconductor optical amplifiers using shaped pulses. <i>Optica</i> , <b>2016</b> , 3, 570	8.6	6
323	Tailoring the photoluminescence polarization anisotropy of a single InAs quantum dash by a post-growth modification of its dielectric environment. <i>Journal of Applied Physics</i> , <b>2016</b> , 120, 074303	2.5	7
322	Exciton spin relaxation in InAs/InGaAlAs/InP(001) quantum dashes emitting near 1.55 $\mu\text{m}$ . <i>Applied Physics Letters</i> , <b>2016</b> , 109, 193108	3.4	8
321	Single-photon emission of InAs/InP quantum dashes at 1.55 $\mu\text{m}$ and temperatures up to 80 K. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 163108	3.4	26
320	Strong attachment of circadian pacemaker neurons on modified ultrananocrystalline diamond surfaces. <i>Materials Science and Engineering C</i> , <b>2016</b> , 64, 278-285	8.3	10
319	Functionalization of nanocrystalline diamond films with phthalocyanines. <i>Applied Surface Science</i> , <b>2016</b> , 379, 415-423	6.7	3
318	Plasma surface fluorination of ultrananocrystalline diamond films. <i>Surface and Coatings Technology</i> , <b>2016</b> , 302, 448-453	4.4	11
317	III-V integration on Si for photonics <b>2016</b> ,		2
316	High-density 1.54 $\mu\text{m}$ InAs/InGaAlAs/InP(100) based quantum dots with reduced size inhomogeneity. <i>Journal of Crystal Growth</i> , <b>2015</b> , 425, 299-302	1.6	27
315	Interface structure and strain state of InAs nano-clusters embedded in silicon. <i>Acta Materialia</i> , <b>2015</b> , 90, 133-139	8.4	11
314	Magnetic field control of the neutral and charged exciton fine structure in single quantum dashes emitting at 1.55 $\mu\text{m}$ . <i>Applied Physics Letters</i> , <b>2015</b> , 106, 053114	3.4	20

313	Electron and hole g factors in InAs/InAlGaAs self-assembled quantum dots emitting at telecom wavelengths. <i>Physical Review B</i> , <b>2015</b> , 92,	3.3	19
312	Site-controlled growth of GaAs nanoislands on pre-patterned silicon substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2015</b> , 212, 443-448	1.6	4
311	Nonlinear pulse propagation in InAs/InP quantum dot optical amplifiers: Rabi oscillations in the presence of nonresonant nonlinearities. <i>Physical Review B</i> , <b>2015</b> , 91,	3.3	13
310	Breakthroughs in Photonics 2014: Time-Scale-Dependent Nonlinear Dynamics in InAs/InP Quantum Dot Gain Media: From High-Speed Modulation to Coherent Light-Matter Interactions. <i>IEEE Photonics Journal</i> , <b>2015</b> , 7, 1-7	1.8	
309	Cell adhesion and growth on ultrananocrystalline diamond and diamond-like carbon films after different surface modifications. <i>Applied Surface Science</i> , <b>2014</b> , 297, 95-102	6.7	40
308	Rabi oscillations in a room-temperature quantum dash semiconductor optical amplifier. <i>Physical Review B</i> , <b>2014</b> , 90,	3.3	19
307	Carrier dynamics in inhomogeneously broadened InAs/AlGaInAs/InP quantum-dot semiconductor optical amplifiers. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 121104	3.4	13
306	Coherent control in a semiconductor optical amplifier operating at room temperature. <i>Nature Communications</i> , <b>2014</b> , 5, 5025	17.4	14
305	High Speed 1.55 $\mu\text{m}$ InAs/InGaAlAs/InP Quantum Dot Lasers. <i>IEEE Photonics Technology Letters</i> , <b>2014</b> , 26, 11-13	2.2	29
304	Low-density InP-based quantum dots emitting around the 1.5 $\mu\text{m}$ telecom wavelength range. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 022113	3.4	16
303	Nanostructured hybrid material based on highly mismatched III-V nanocrystals fully embedded in silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2014</b> , 211, 817-822	1.6	6
302	Phonon-assisted radiative recombination of excitons confined in strongly anisotropic nanostructures. <i>Physical Review B</i> , <b>2014</b> , 90,	3.3	18
301	Single photon emission at 1.55 $\mu\text{m}$ from charged and neutral exciton confined in a single quantum dash. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 021909	3.4	33
300	Static and dynamic characteristics of InAs/AlGaInAs/InP quantum dot lasers operating at 1550 nm <b>2013</b> ,		1
299	Bright light emissions with narrow spectral linewidths from single InAs/GaAs quantum dots directly grown on silicon substrates. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 132101	3.4	5
298	Electronic structure, morphology and emission polarization of enhanced symmetry InAs quantum-dot-like structures grown on InP substrates by molecular beam epitaxy. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 094306	2.5	25
297	Investigation of NV centers in nano- and ultrananocrystalline diamond pillars. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2013</b> , 210, 2066-2073	1.6	10
296	Telecom-wavelength (1.5 $\mu\text{m}$ ) single-photon emission from InP-based quantum dots. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 162101	3.4	87

295	Grafting of manganese phthalocyanine on nanocrystalline diamond films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2013</b> , 210, 2048-2054	1.6	12
294	Heterodyne pump probe measurements of nonlinear dynamics in an indium phosphide photonic crystal cavity. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 181120	3.4	24
293	Nonlinear pulse propagation in a quantum dot laser. <i>Optics Express</i> , <b>2013</b> , 21, 5715-36	3.3	5
292	Reactive ion etching of nanocrystalline diamond for the fabrication of one-dimensional nanopillars. <i>Diamond and Related Materials</i> , <b>2013</b> , 36, 58-63	3.5	11
291	High-gain wavelength-stabilized 1.55 $\mu\text{m}$ InAs/InP(100) based lasers with reduced number of quantum dot active layers. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 221117	3.4	20
290	Investigation of NV centers in diamond nanocrystallites and nanopillars. <i>Physica Status Solidi (B): Basic Research</i> , <b>2013</b> , 250, 48-50	1.3	3
289	Rabi oscillations and self-induced transparency in InAs/InP quantum dot semiconductor optical amplifier operating at room temperature. <i>Optics Express</i> , <b>2013</b> , 21, 26786-96	3.3	25
288	<b>2013</b> ,		1
287	Exciton and biexciton dynamics in single self-assembled InAs/InGaAlAs/InP quantum dash emitting near 1.55 $\mu\text{m}$ . <i>Applied Physics Letters</i> , <b>2013</b> , 103, 253113	3.4	26
286	All-optical signal processing at 10 GHz using a photonic crystal molecule. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 193510	3.4	18
285	Direct growth of III $\nu$ quantum dots on silicon substrates: structural and optical properties. <i>Semiconductor Science and Technology</i> , <b>2013</b> , 28, 094004	1.8	12
284	Two-color switching and wavelength conversion at 10 GHz using a Photonic Crystal molecule <b>2013</b> ,		1
283	Pre-patterned silicon substrates for the growth of III $\nu$ nanostructures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2012</b> , 209, 2402-2410	1.6	10
282	Influence of the surface termination of ultrananocrystalline diamond/amorphous carbon composite films on their interaction with neurons. <i>Diamond and Related Materials</i> , <b>2012</b> , 26, 60-65	3.5	16
281	Nanostructuring of silicon substrates for the site-controlled growth of GaAs/In <sub>0.15</sub> Ga <sub>0.85</sub> As/GaAs nanostructures. <i>Microelectronic Engineering</i> , <b>2012</b> , 97, 59-63	2.5	4
280	15-W Fiber-Coupled Quantum-Dot Pump Module. <i>IEEE Photonics Technology Letters</i> , <b>2012</b> , 24, 1030-1032.2		
279	<b>2012</b> ,		1
278	High-Speed Low-Noise InAs/InAlGaAs/InP 1.55- $\mu\text{m}$ Quantum-Dot Lasers. <i>IEEE Photonics Technology Letters</i> , <b>2012</b> , 24, 809-811	2.2	21



277	Height-driven linear polarization of the surface emission from quantum dashes. <i>Semiconductor Science and Technology</i> , <b>2012</b> , 27, 105022	1.8	12
276	Low temperature growth of nanocrystalline and ultrananocrystalline diamond films: A comparison. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2012</b> , 209, 1664-1674	1.6	21
275	Single-photon emission from single InGaAs/GaAs quantum dots grown by droplet epitaxy at high substrate temperature. <i>Nanoscale Research Letters</i> , <b>2012</b> , 7, 493	5	9
274	Stability of the surface termination of differently modified ultrananocrystalline diamond/amorphous carbon composite films. <i>Surface and Coatings Technology</i> , <b>2012</b> , 209, 184-189	4.4	10
273	Gas chopping etching process for InP based nanostructures with high aspect ratios. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2012</b> , 30, 060601	1.3	
272	Extreme nonlinearities in InAs/InP nanowire gain media: the two-photon induced laser. <i>Optics Express</i> , <b>2012</b> , 20, 5987-92	3.3	9
271	Complex characterization of short-pulse propagation through InAs/InP quantum-dash optical amplifiers: from the quasi-linear to the two-photon-dominated regime. <i>Optics Express</i> , <b>2012</b> , 20, 347-53	3.3	7
270	Influence of electronic coupling on the radiative lifetime in the (In,Ga)As/GaAs quantum dot/quantum well system. <i>Physical Review B</i> , <b>2012</b> , 85,	3.3	25
269	On the mechanisms of energy transfer between quantum well and quantum dashes. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 033520	2.5	6
268	Growth-Temperature Dependence of Wetting Layer Formation in High Density InGaAs/GaAs Quantum Dot Structures Grown by Droplet Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 085501	1.4	2
267	Tribological properties of nanocrystalline diamond films deposited by hot filament chemical vapor deposition. <i>AIP Advances</i> , <b>2012</b> , 2, 032164	1.5	16
266	Growth-Temperature Dependence of Wetting Layer Formation in High Density InGaAs/GaAs Quantum Dot Structures Grown by Droplet Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 085501	1.4	2
265	Nanocrystalline diamond containing hydrogels and coatings for acceleration of osteogenesis. <i>Diamond and Related Materials</i> , <b>2011</b> , 20, 165-169	3.5	15
264	Plasma amination of ultrananocrystalline diamond/amorphous carbon composite films for the attachment of biomolecules. <i>Diamond and Related Materials</i> , <b>2011</b> , 20, 254-258	3.5	20
263	Surface Functionalization of Plasma Treated Ultrananocrystalline Diamond/Amorphous Carbon Composite Films. <i>NATO Science for Peace and Security Series B: Physics and Biophysics</i> , <b>2011</b> , 463-469	0.2	1
262	1.3- $\mu\text{m}$ Two-Section DBR Lasers Based on Surface Defined Gratings for High-Speed Telecommunication. <i>IEEE Photonics Technology Letters</i> , <b>2011</b> , 23, 411-413	2.2	7
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2	Quantum-dot microlasers as high-speed light sources for monolithic integration		1
1	Tailored InP-based quantum dash structures for ultra-wide gain bandwidth applications		1